

New Perspectives in *ab initio* Calculations for Semiconducting Oxides

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Outline

1 LAOSTO

2 VO₂



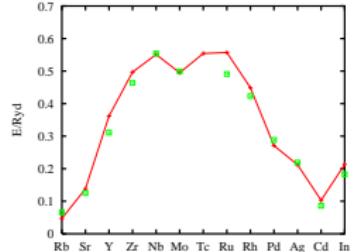
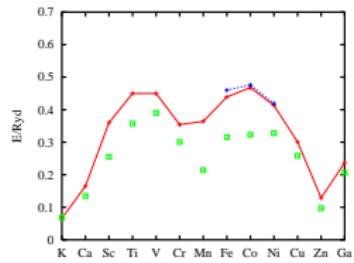
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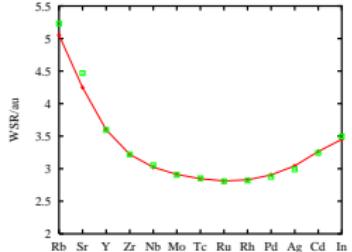
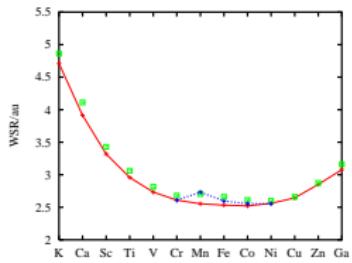
2 VO₂

Calculated Electronic Properties

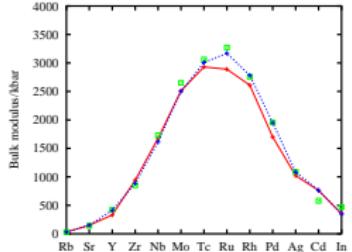
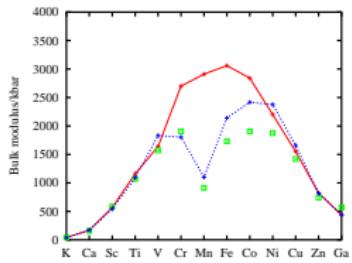
Moruzzi, Janak, Williams (IBM, 1978)



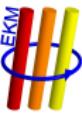
Cohesive Energies
 $\hat{=}$ Stability



Wigner-Seitz-Rad.
 $\hat{=}$ Volume

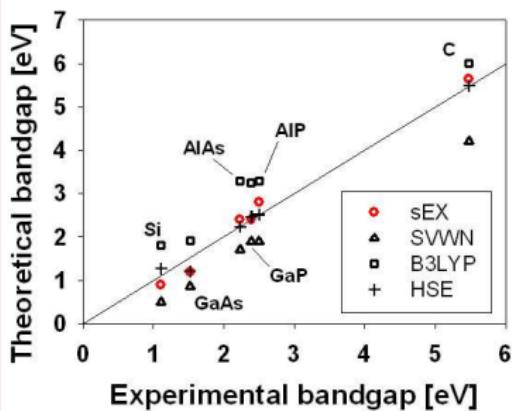


Compressibility
 $\hat{=}$ Hardness



Energy band structures from screened HF exchange

Si, AlP, AlAs, GaP, and GaAs



Experimental and theoretical bandgap properties

Shimazaki, Asai
JCP **132**, 224105 (2010)

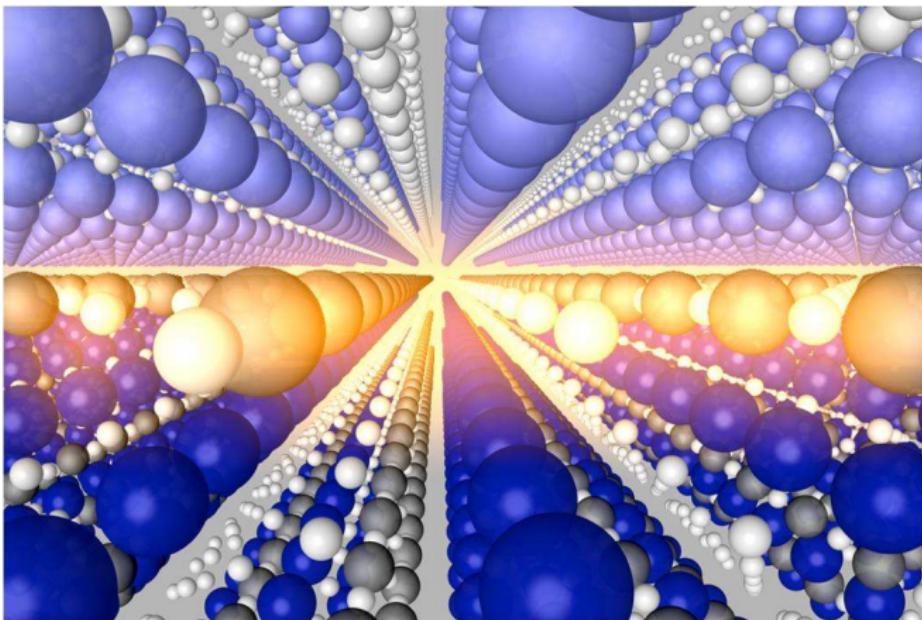


Outline

1 LAOSTO

2 VO₂

2D Electron Gas at LaAlO₃-SrTiO₃ Interface



2D Electron Gas at LaAlO₃-SrTiO₃ Interface

Issues

- Role of electronic correlations?
 - SrTiO₃, LaAlO₃: band insulators
 - SrTiO₃/LaAlO₃ interface: MIT (# LaAlO₃ layers)
 - magnetic properties of the interface
 - superconductivity below ≈ 200 mK
- What is the origin of the 2-DEG?
 - intrinsic mechanism?
 - defect-doping?

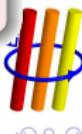


Slab Calculations for the LaAlO₃-SrTiO₃ Interface



Structural setup of calculations

- central region: 5 layers SrTiO₃, TiO₂-terminated
- sandwiches: 2 to 5 layers LaAlO₃, AlO₂ surface
- vacuum region $\approx 20 \text{ \AA}$
- inversion symmetry
- lattice constant of SrTiO₃ from GGA (3.944 Å)



Slab Calculations for the LaAlO₃-SrTiO₃ Interface



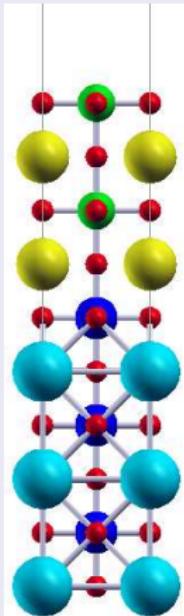
Calculational method

- Vienna Ab Initio Simulation Package (VASP)
- GGA-PBE
- Steps:
 - 1 optimization of SrTiO₃ lattice constant
 - 2 slab calculations
 - full relaxation of all atomic positions
 - $5 \times 5 \times 1$ \mathbf{k} -points
 - Γ -centered \mathbf{k} -mesh
 - Methfessel-Paxton BZ-integration

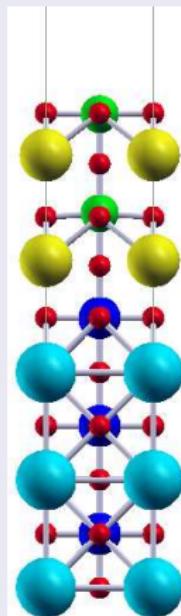


Slab Calculations for the LaAlO₃-SrTiO₃ Interface

Ideal

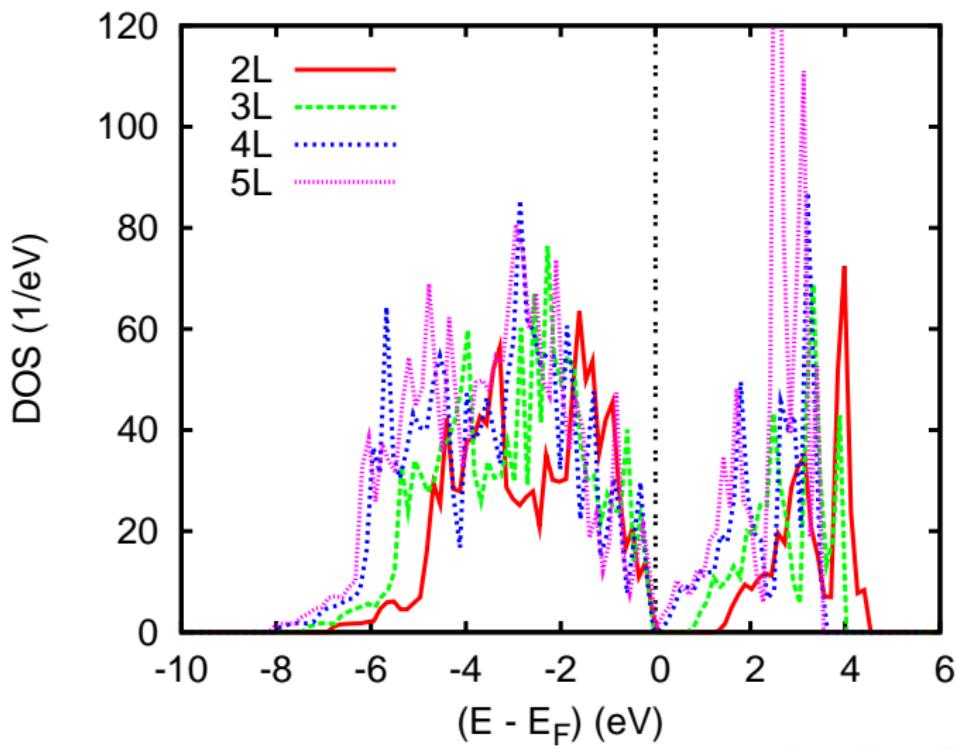


Optimized



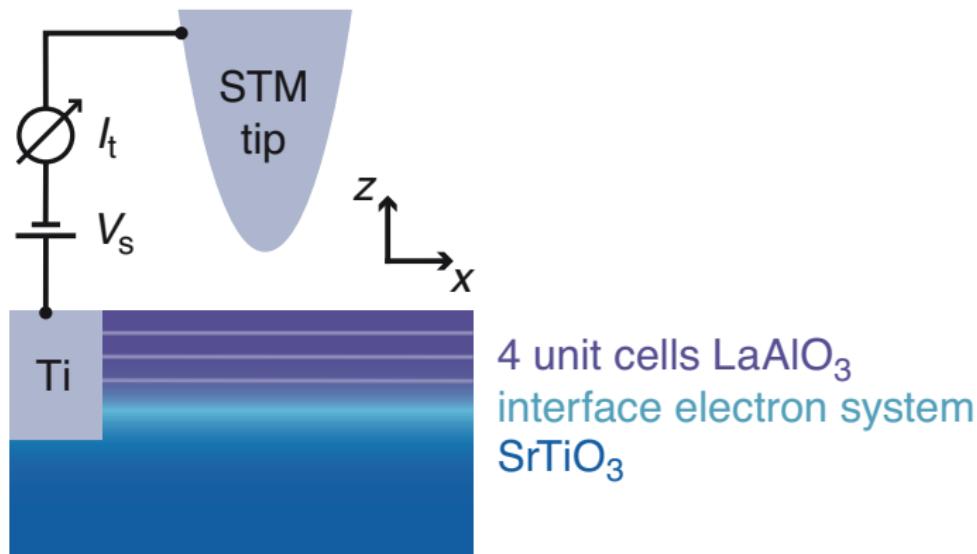
Structural relaxation

- AlO₂ surface layers
 - strong inward relaxation
 - weak buckling
- LaO layers
 - strong buckling
- AlO₂ subsurface layers
 - buckling
- TiO₂ interface layers
 - small outward relaxation

Slab Calculations for the LaAlO₃-SrTiO₃ Interface

Tunneling Spectroscopy of LaAlO₃-SrTiO₃ Interface

What is the origin of the 2-DEG?
Intrinsic mechanism or defect-doping?

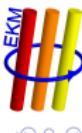
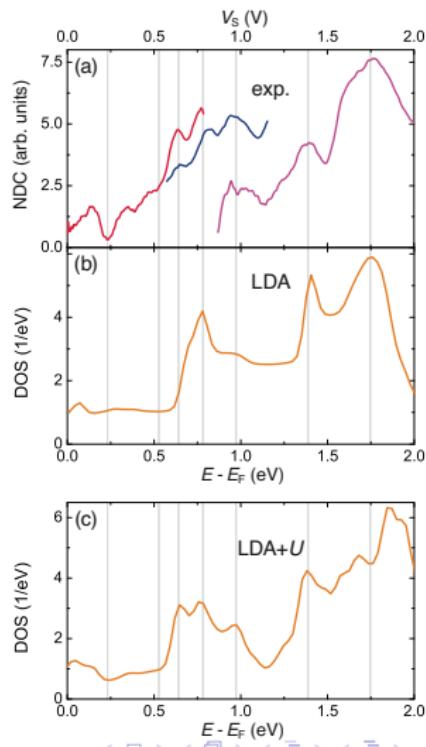


M. Breitschaft *et al.*, PRB **81**, 153414 (2010)



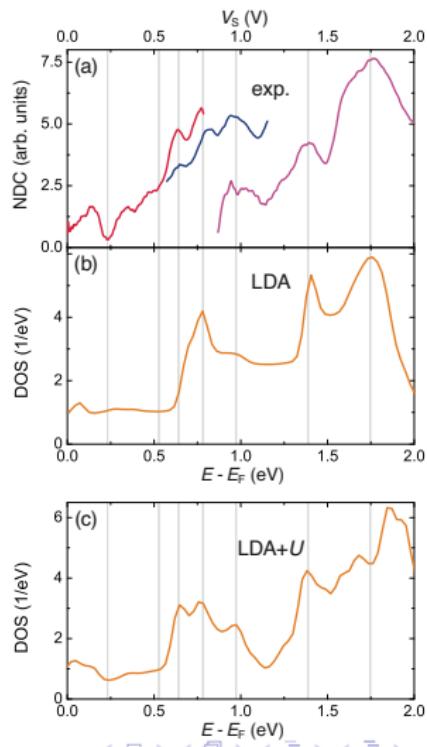
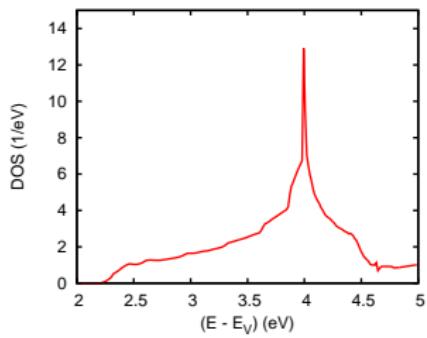
Tunneling Spectroscopy of LaAlO₃-SrTiO₃ Interface

- 4uc LaAlO₃ on SrTiO₃, tunneling data
- 4uc LaAlO₃ on SrTiO₃, LDA calculations, DOS of interface Ti
- 4uc LaAlO₃ on SrTiO₃, LDA+U calculations, DOS of interface Ti

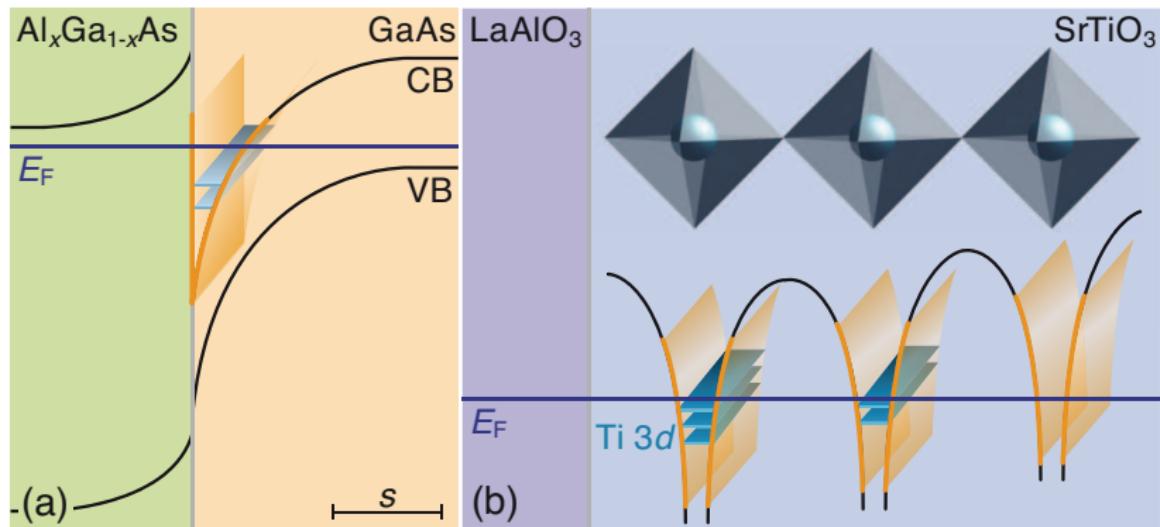


Tunneling Spectroscopy of LaAlO₃-SrTiO₃ Interface

- bulk SrTiO₃,
LDA calculations,
conduction band DOS



"2D Electron Liquid State" at LaAlO₃-SrTiO₃ Interface



M. Breitschaft *et al.*, PRB **81**, 153414 (2010)



Critical review of the Local Density Approximation

Limitations and Beyond

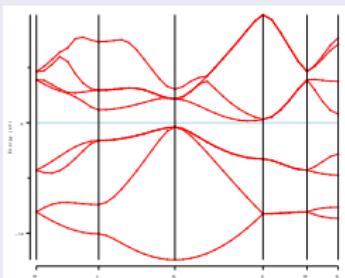
- LDA **exact** for homogeneous electron gas (within QMC)
- Spatial variation of ρ **ignored**
 - include $\nabla\rho(\mathbf{r}), \dots$
 - Generalized Gradient Approximation (GGA)
- Self-interaction cancellation in $v_{Hartree} + v_x$ **violated**
 - **repair** using exact Hartree-Fock exchange functional
 - hybrid functionals (PBE0, HSE03, HSE06)

Critical review of the Local Density Approximation

Limitations and Beyond

- Self-interaction cancellation in $v_{\text{Hartree}} + v_x$ violated
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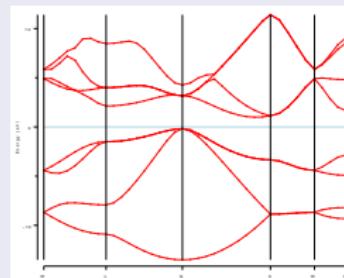
GGA



Si bandgap

- exp: 1.11 eV
- GGA: 0.57 eV
- HSE: 1.15 eV

HSE

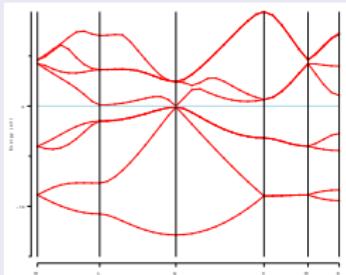


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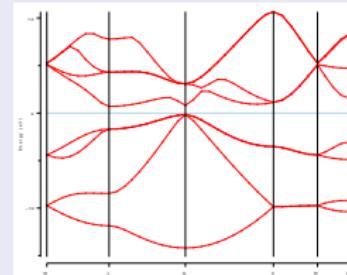
GGA



Ge bandgap

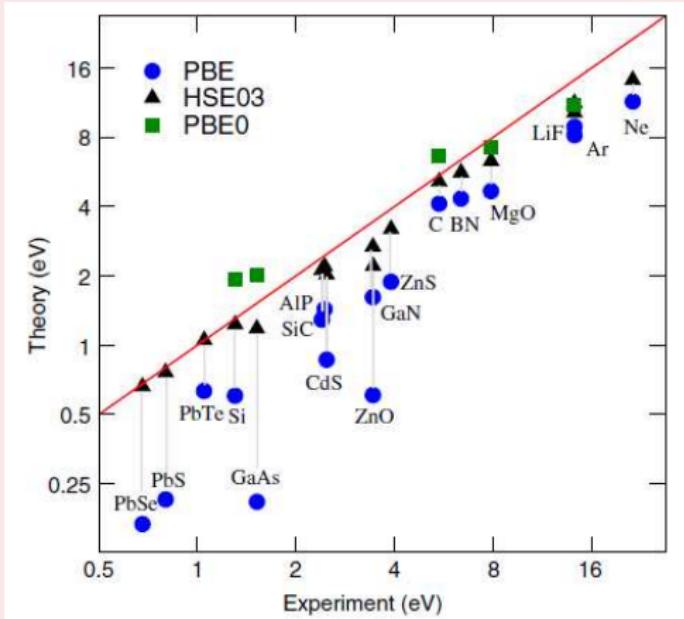
- exp: 0.67 eV
- GGA: 0.09 eV
- HSE: 0.66 eV

HSE



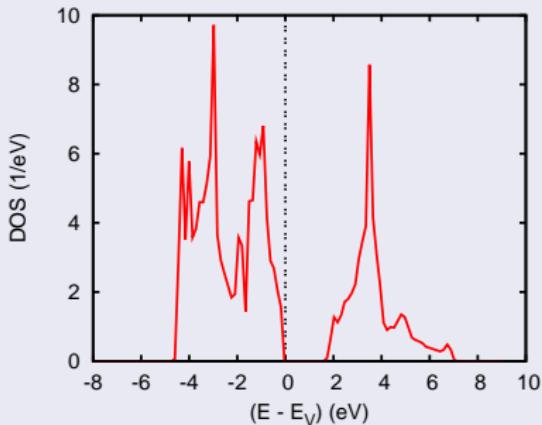
Critical review of the Local Density Approximation

Calculated vs. experimental bandgaps



SrTiO₃

GGA



Bandgap

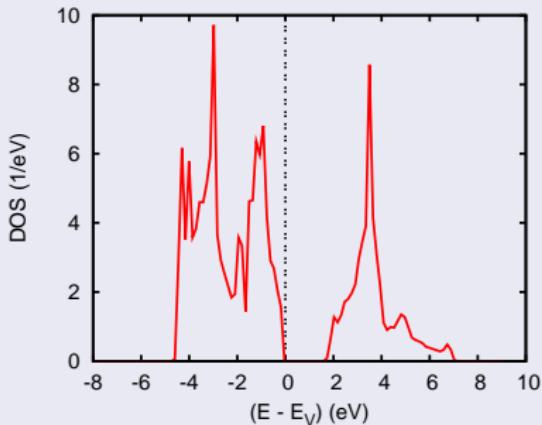
GGA: ≈ 1.6 eV,

exp.: 3.2 eV

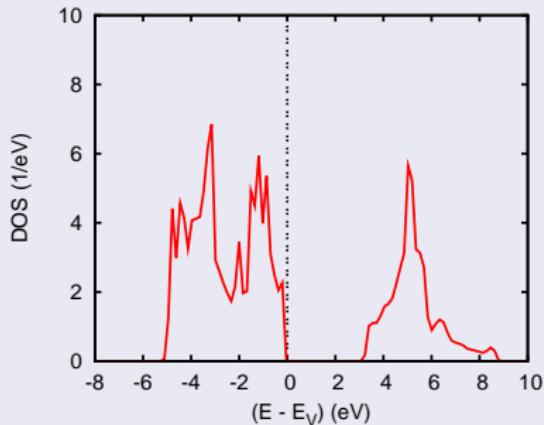


SrTiO₃

GGA



HSE

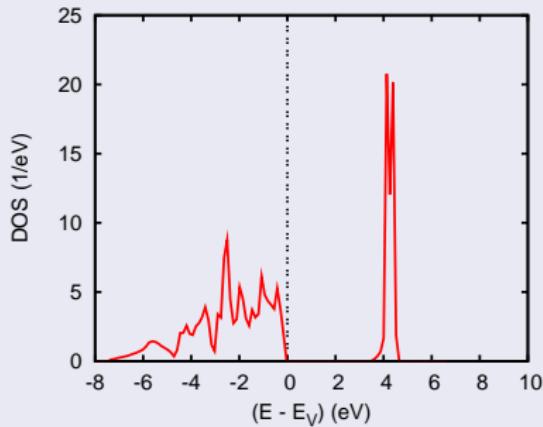


Bandgap

GGA: ≈ 1.6 eV, HSE: ≈ 3.1 eV, exp.: 3.2 eV

LaAlO₃

GGA



Bandgap

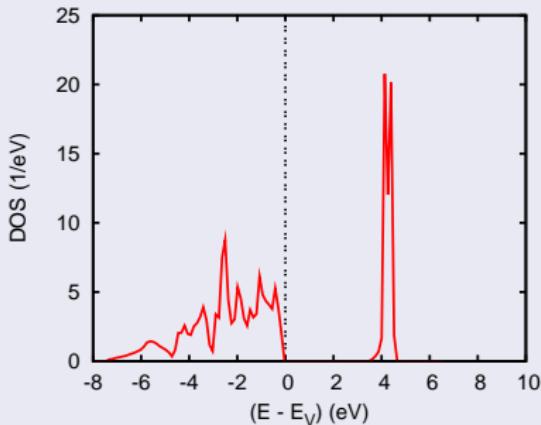
GGA: ≈ 3.5 eV,

exp.: 5.6 eV

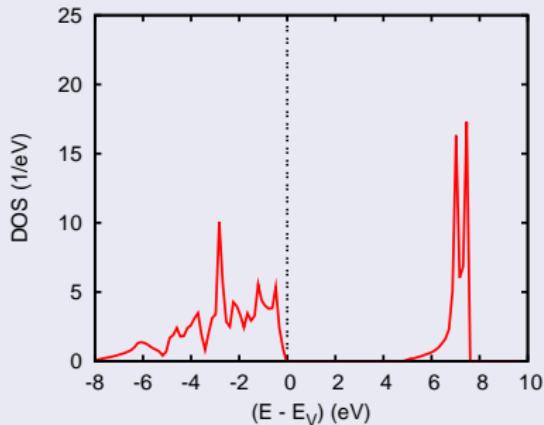


LaAlO₃

GGA



HSE



Bandgap

GGA: ≈ 3.5 eV, HSE: ≈ 5.0 eV, exp.: 5.6 eV

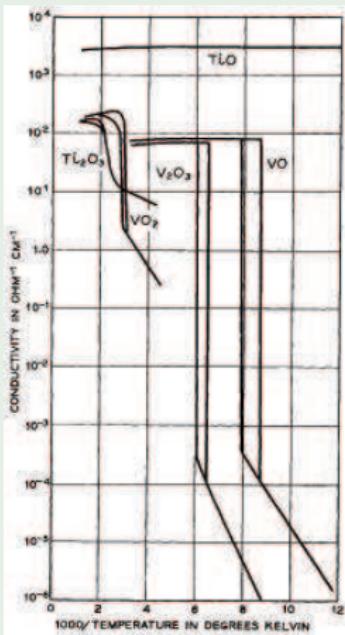
Outline

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2 VO₂

Metal-Insulator Transition of VO₂

Morin, PRL 1959



Metal-Insulator Transitions (MIT)

- VO₂ (d^1)
 - 1st order, 340 K, $\Delta\sigma \approx 10^4$
 - rutile \rightarrow M₁ (monoclinic)
- V₂O₃ (d^2)
 - 1st order, 170 K, $\Delta\sigma \approx 10^6$
 - corundum \rightarrow monoclinic
 - paramagn. \rightarrow AF order

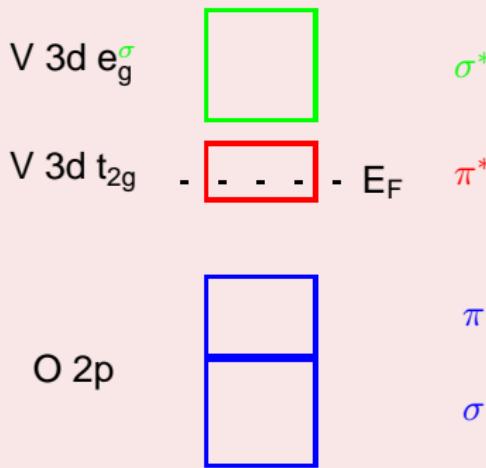
Origin of the MIT???

- Structural Changes?
- Electron Correlations?



Metal-Insulator Transition of VO₂

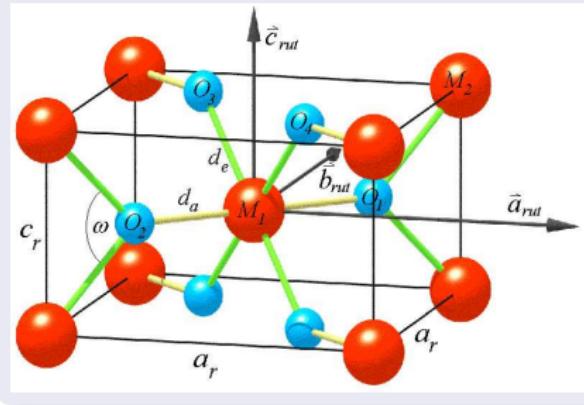
Octahedral Coordination



- V 3d-O 2p hybridization
 - σ, σ* ($p-de_g^\sigma$)
 - π, π* ($p-dt_{2g}$)

Rutile Structure

- simple tetragonal
- P4₂/mnm (D_{4h}¹⁴)



Metal-Insulator Transition of VO₂

Octahedral Coordination

V 3d e_g^σ



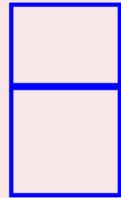
σ*

V 3d t_{2g}



- E_F - π*

O 2p



π

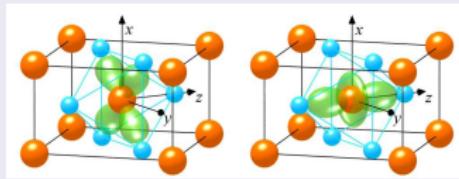
σ

- V 3d-O 2p hybridization

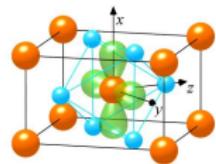
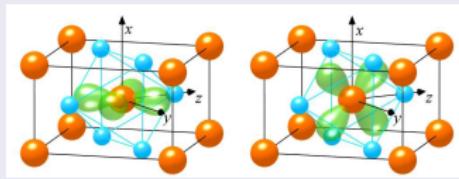
- σ, σ* ($p-de_g^\sigma$)

- π, π* ($p-dt_{2g}$)

e_g^σ Orbitals

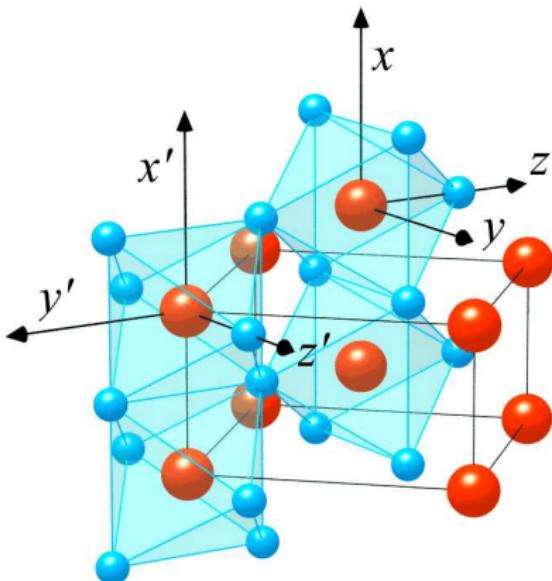


t_{2g} Orbitals



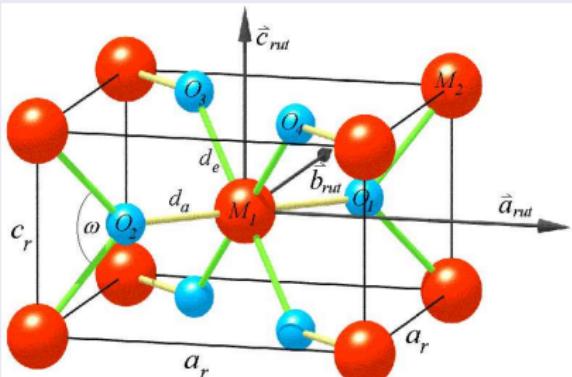
Metal-Insulator Transition of VO₂

Octahedral Chains



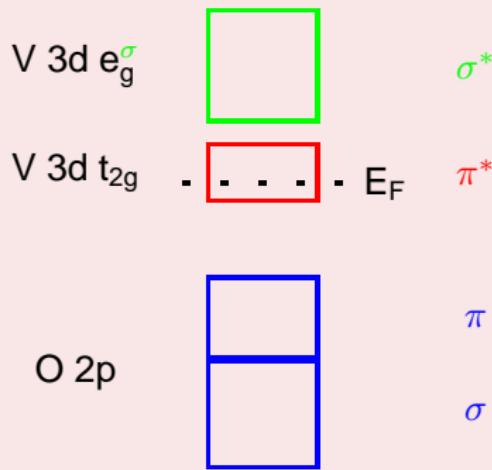
Rutile Structure

- simple tetragonal
- P4₂/mnm (D_{4h}^{14})

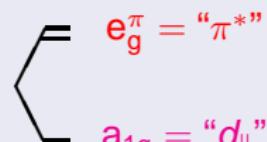
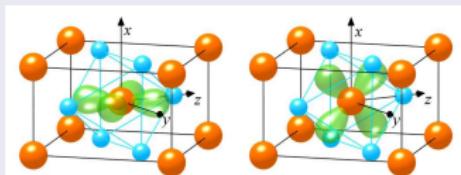
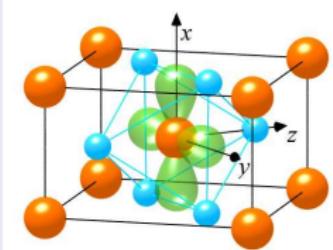


Metal-Insulator Transition of VO₂

Octahedral Coordination

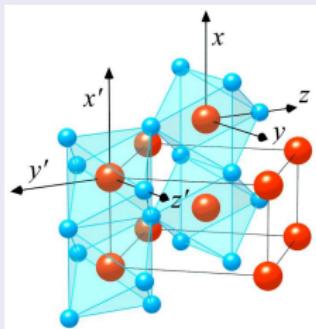


t_{2g} Orbitals

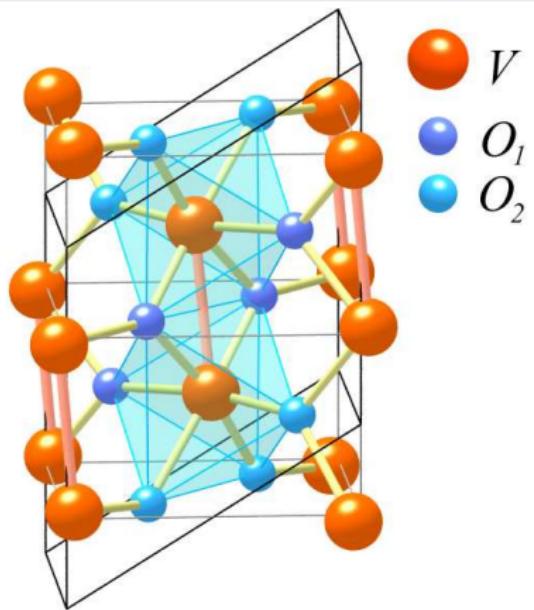
 $e_g^\pi = \text{"}\pi\text{*}"$ $a_{1g} = \text{"}\sigma\text{||}"$ 

Metal-Insulator Transition of VO₂

Rutile Structure



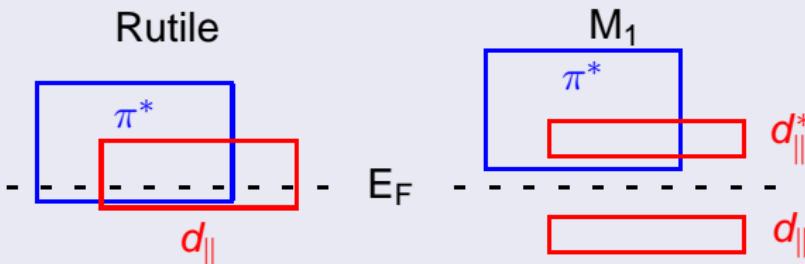
M₁-Structure



Structural Changes

- V-V dimerization $\parallel c_R$
- antiferroelectric displacement $\perp c_R$

Metal-Insulator Transition of VO₂



- Goodenough, 1960-1972
 - metal-metal dimerization $\parallel c_R \rightarrow$ splitting into $d_{\parallel}, d_{\parallel}^*$
 - antiferroelectric displacement $\perp c_R \rightarrow$ upshift of π^*
- Zylbersztein and Mott, 1975
 - splitting of d_{\parallel} by electronic correlations
 - upshift of π^* unscreened d_{\parallel} electrons



Metal-Insulator Transition of VO₂

Other Compounds

	d ⁰	d ¹	d ²	d ³	d ⁴	d ⁵	d ⁶
3d	TiO ₂ (S)	VO ₂ [*] (M-S)	CrO ₂ (F-M)	MnO ₂ (AF-S)			
4d		NbO ₂ [*] (M-S)	MoO ₂ [*] (M)	TcO ₂ [*] (M)	RuO ₂ (M)	RhO ₂ (M)	
5d		TaO ₂ (?)	WO ₂ [*] (M)	ReO ₂ [*] (M)	OsO ₂ (M)	IrO ₂ (M)	PtO ₂ [*] (M)

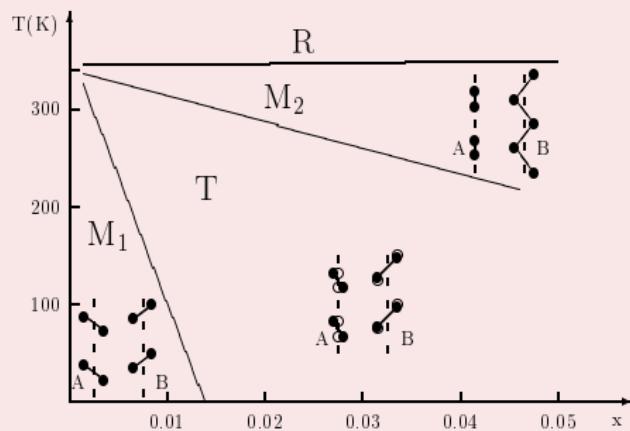
* deviations from rutile, M = metal, S = semiconductor

F/AF = ferro-/antiferromagnet



Metal-Insulator Transition of VO₂

Other Phases



- doping with Cr, Al, Fe, Ga
- uniaxial pressure $\parallel \langle 110 \rangle$

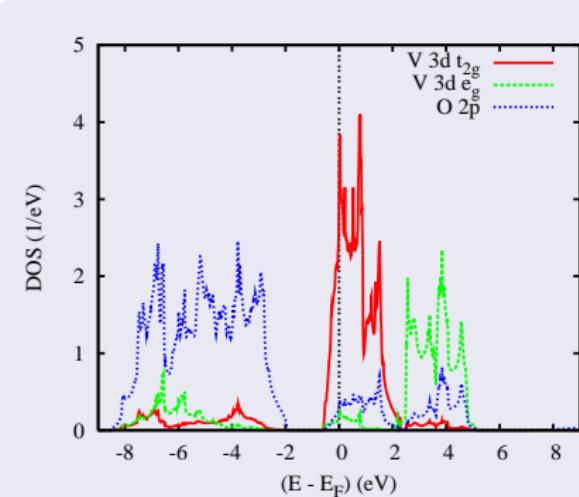
Cr_xV_{1-x}O₂
Pouget, Launois, 1976



Electronic Structure in Detail

Rutile Structure

- molecular-orbital picture ✓
- octahedral crystal field
 \Rightarrow V 3d t_{2g}/e_g
- V 3d–O 2p hybridization



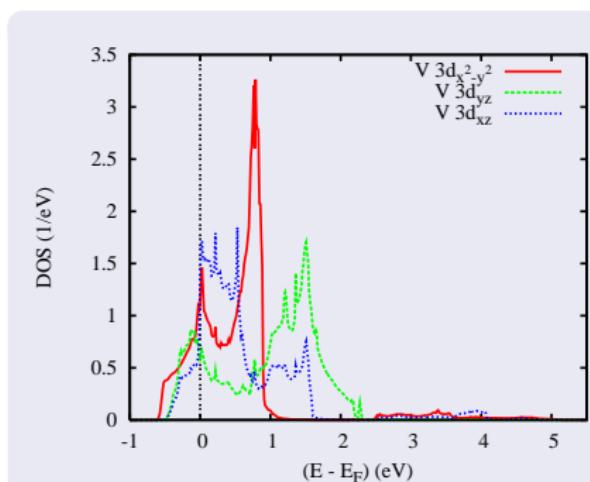
VE, Ann. Phys. (Leipzig) 11, 650 (2002)



Electronic Structure in Detail

Rutile Structure

- molecular-orbital picture ✓
- octahedral crystal field
 \implies V 3d t_{2g} / e_g
- V 3d–O 2p hybridization
- t_{2g} at E_F : $d_{x^2-y^2}$, d_{yz} , d_{xz}
- $n(d_{x^2-y^2}) \approx n(d_{yz}) \approx n(d_{xz})$

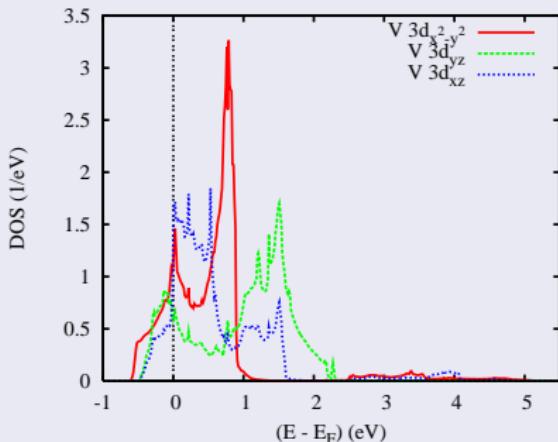


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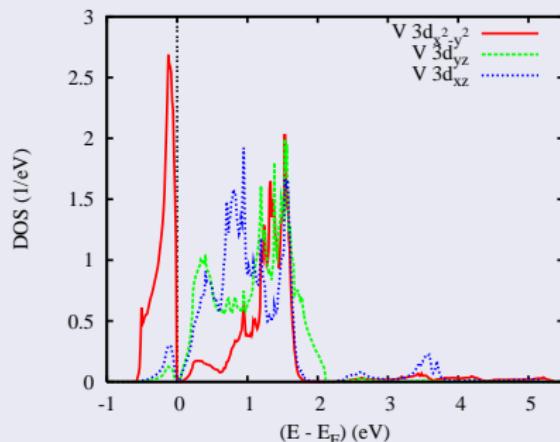


Electronic Structure in Detail

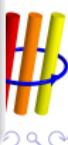
Rutile Structure



M₁ Structure



- bonding-antibonding splitting of d_{\parallel} bands
- energetical upshift of π^* bands \Rightarrow orbital ordering
- optical band gap on the verge of opening



Further investigations

Cluster-DMFT Calculations

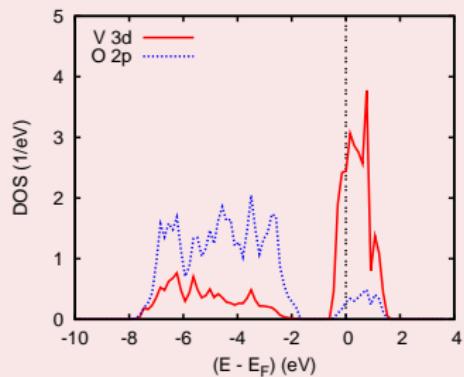
- Rutile-VO₂
 - moderately correlated metal
- M₁-VO₂
 - correlations strong/weak on $d_{||}/\pi^*$
 - optical band gap of 0.6 eV
- Phase Transition
 - “correlation-assisted Peierls transition”

S. Biermann, A. Poteryaev, A. I. Lichtenstein, A. Georges
PRL 94, 026404 (2005)

New Calculations: GGA vs. HSE

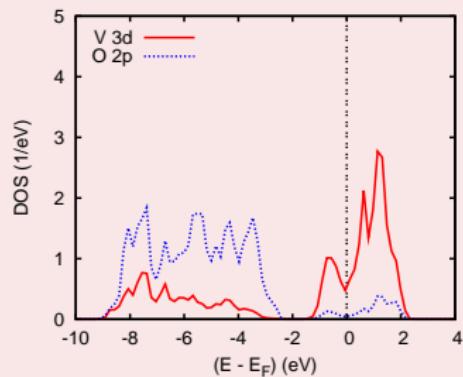
Rutile Structure

GGA



Rutile Structure

HSE

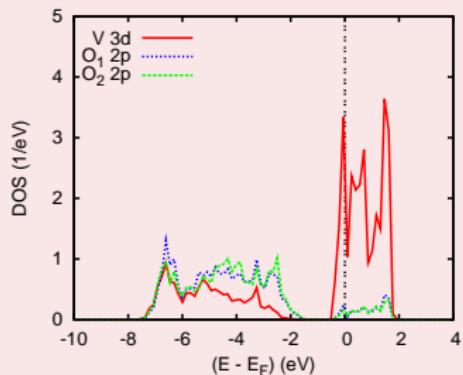
Rutile Structure: GGA \Rightarrow HSE

- broadening of O 2p and V 3d t_{2g} (!) bands
- splitting within V 3d t_{2g} bands

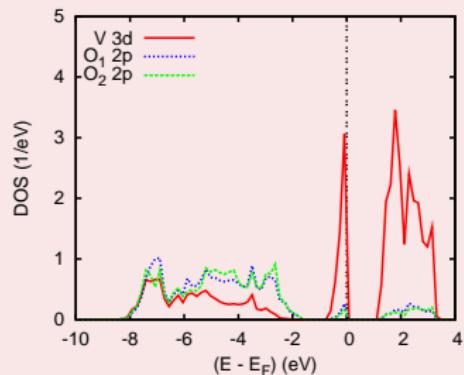
New Calculations: GGA vs. HSE

M₁ Structure

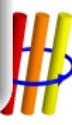
GGA

M₁ Structure

HSE

M₁ Structure: GGA \Rightarrow HSE

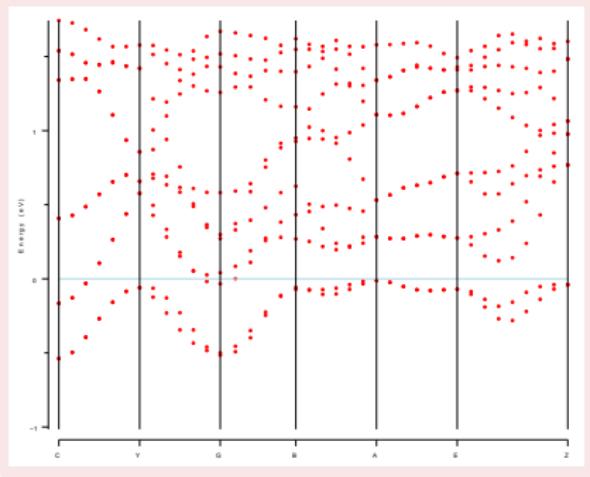
- splitting of d_{\parallel} bands, upshift of π^* bands
- optical bandgap of ≈ 1 eV



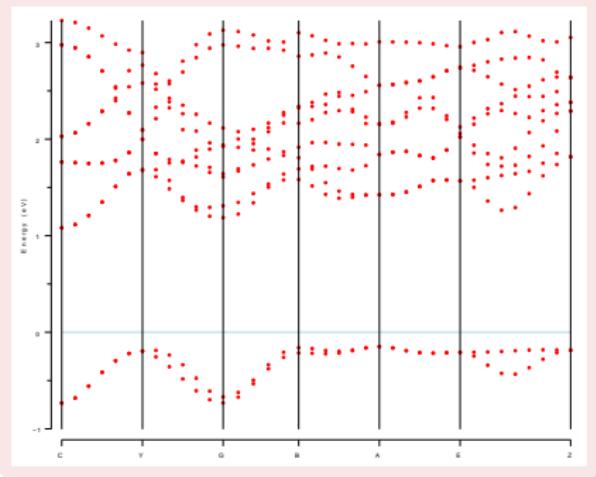
New Calculations: GGA vs. HSE

M₁ Structure

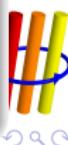
GGA

M₁ Structure

HSE

M₁ Structure: GGA \Rightarrow HSE

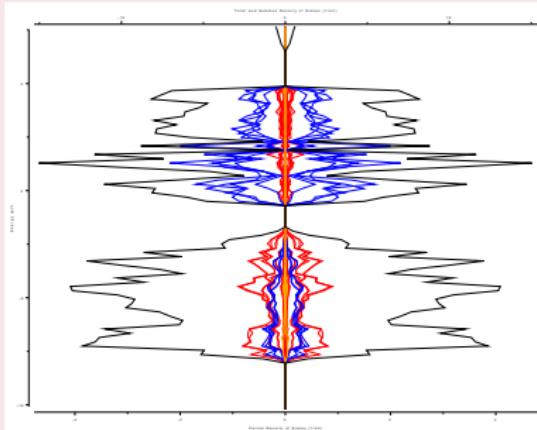
- splitting of d_{\parallel} bands, upshift of π^* bands
- optical bandgap of ≈ 1 eV



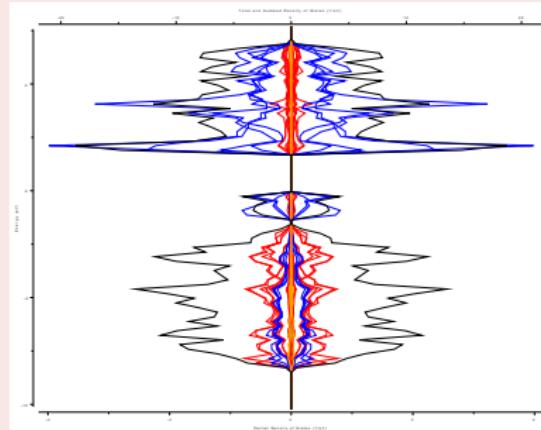
New Calculations: GGA vs. HSE

M₂ Structure

GGA

M₂ Structure

HSE

M₂ Structure: GGA \Rightarrow HSE

- localized magnetic moment of $1 \mu_B$
- optical bandgap of ≈ 1.6 eV



Unified Picture

Rutile-Related Transition-Metal Dioxides

VO₂ (3d¹), NbO₂ (4d¹), MoO₂ (4d²)
(WO₂ (5d²), TcO₂ (4d³), ReO₂ (5d³))

- instability against similar local distortions
 - metal-metal dimerization $\parallel c_R$
 - antiferroelectric displacement $\perp c_R$
- („accidental“) metal-insulator transition of the d¹-members

VE *et al.*, J. Phys.: CM **12**, 4923 (2000)

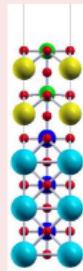
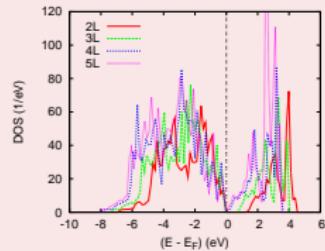
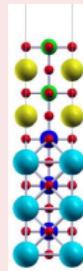
VE, Ann. Phys. **11**, 650 (2002)

VE, EPL **58**, 851 (2002)

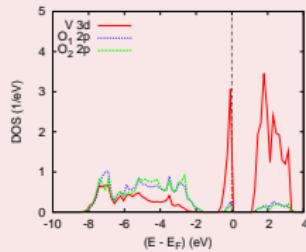
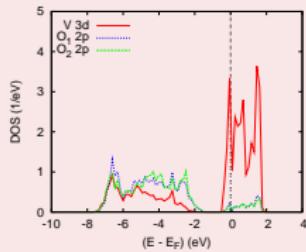
J. Moosburger-Will *et al.*, PRB **79**, 115113 (2009)

Success Stories

LaAlO₃/SrTiO₃



Metal-Insulator Transitions in VO₂



Acknowledgments



Augsburg

M. Breitschaft, U. Eckern,
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J. Moosburger-Will, N. Pavlenko

GEFÖRDERT VOM



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San Diego

Thank You for Your Attention!

